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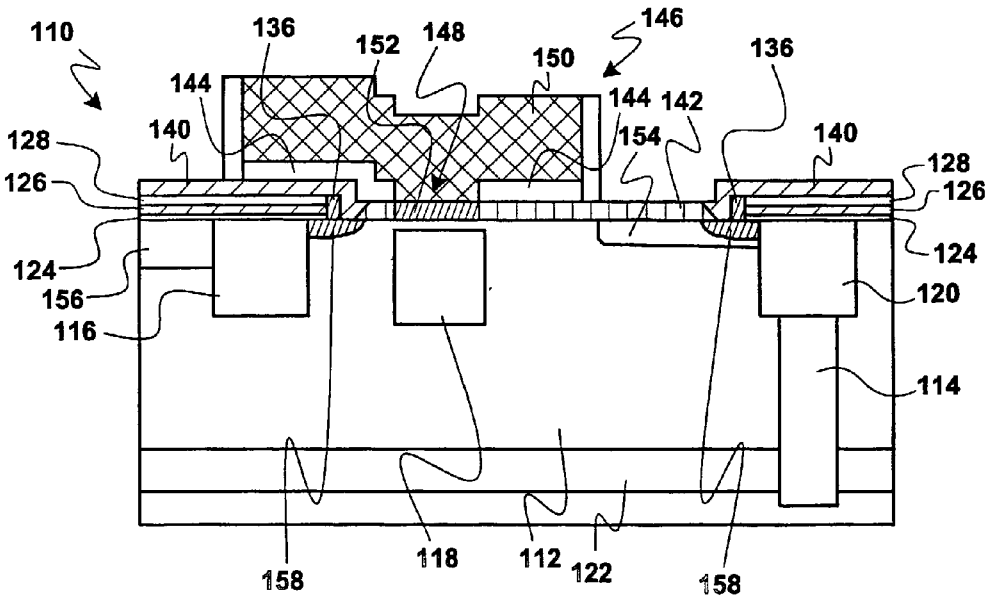
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(54) Title: SELF ALIGNED COMPACT BIPOLAR JUNCTION TRANSISTOR LAYOUT, AND METHOD OF MAKING SAME



(57) Abstract: The invention relates to a process of forming a bipolar junction transistor (BJT) that includes forming a topology over a substrate (112). Thereafter, a spacer (136) is formed at the topology. A base layer (140) is formed from epitaxial silicon above the spacer (136) and at the topology. A leakage block (158) is formed in the substrate by out-diffusion from the spacer (136). Thereafter a BJT is completed with the base layer (140) and the spacer (136).

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